

Claims:

1. A method for dry etching a semiconductor wafer by generating plasma between a power-supplied first electrode and a grounded second electrode, said method comprising the steps of:

5 generating plasma after bring the lower surface of the edge of the wafer in contact with said first electrode, and etching the upper surface and the side surface of the edge of the semiconductor wafer by reactive ion etching (RIE) using ionized species; and

10 generating plasma after bring the upper surface of the edge of the wafer in contact with said second electrode, and etching the lower surface and the side surface of the edge of the semiconductor wafer by plasma etching using radicals.